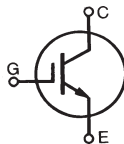


GenX3™ 1200V IGBTs

IXGH32N120A3 IXGT32N120A3

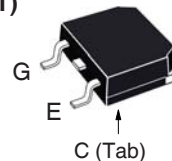
$V_{CES} = 1200V$
 $I_{C110} = 32A$
 $V_{CE(sat)} \leq 2.35V$

Ultra-Low V_{sat} PT IGBTs for up to 3 kHz Switching

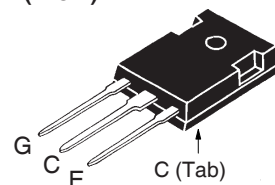


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	75	A
I_{C110}	$T_C = 110^\circ C$	32	A
I_{CM}	$T_C = 25^\circ C$, 1ms	230	A
I_A	$T_C = 25^\circ C$	20	A
E_{AS}	$T_C = 25^\circ C$	120	mJ
SSOA	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 20\Omega$	$I_{CM} = 150$	A
(RBSOA)	Clamped Inductive Load	$V_{CE} \leq 0.8 \cdot V_{CES}$	
P_C	$T_C = 25^\circ C$	300	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.063in) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6.0	g
	TO-268	4.0	g

TO-268 (IXGT)



TO-247 (IXGH)



G = Gate C = Collector
 E = Emitter Tab = Collector

Features

- Optimized for Low Conduction Losses
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

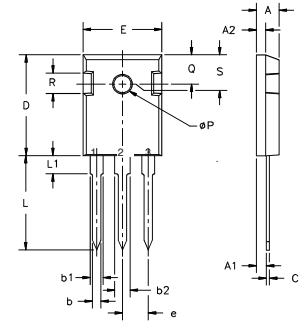
- Power Inverters
- Capacitor Discharge
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 1 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C110}$, $V_{GE} = 15V$, Note 1			2.35 V
	$I_C = 400A$, $V_{GE} = 30V$, Note 1		11	V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 50\text{A}$, $V_{CE} = 10\text{V}$, Note 1	14	20	S
$I_{C(on)}$	$V_{CE} = 10\text{V}$, $V_{GE} = 15\text{V}$, Note 1		94	A
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		2150	pF
C_{oes}			130	pF
C_{res}			14	pF
Q_g	$I_C = 50\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		89	nC
Q_{ge}			15	nC
Q_{gc}			34	nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $V_{GE} = 20\text{V}$, $V_{CE} = 0.8 \cdot V_{CES}$, $I_C = 100\text{A}$ $R_G = 10\Omega$ (External)		39	ns
t_r			200	ns
$t_{d(off)}$			140	ns
t_f			1240	ns
R_{thJC}	TO-247			0.42 $^\circ\text{C/W}$
R_{thCK}			0.21	$^\circ\text{C/W}$

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

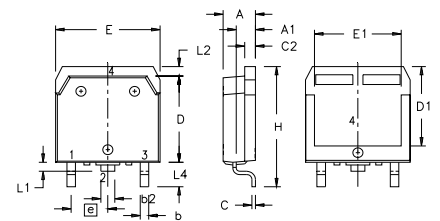
TO-247 AD Outline



Terminals: 1 - Gate 2 - Collector
3 - Emitter

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Terminals: 1 - Gate 2, 4 - Collector
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010	BSC	0.25	BSC
L ₄	.150	.161	3.80	4.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

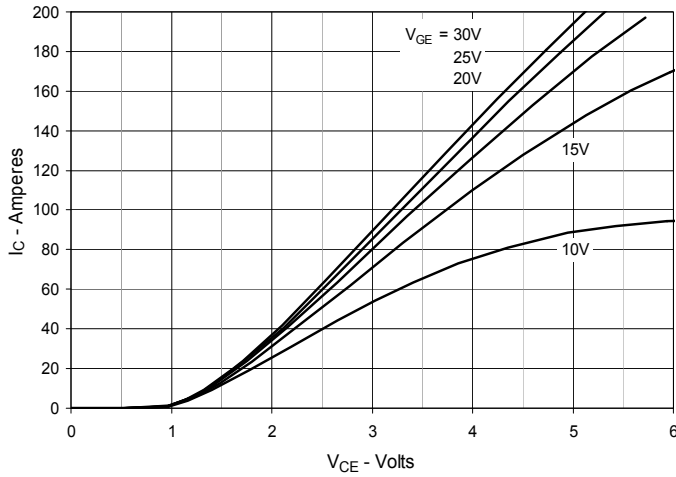


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

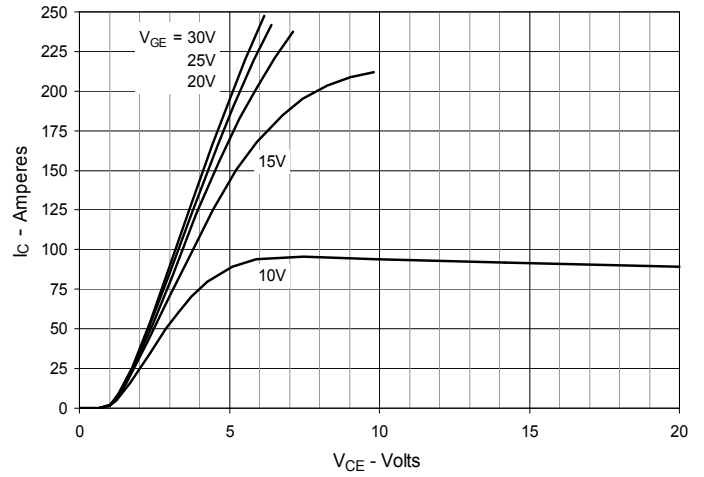


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

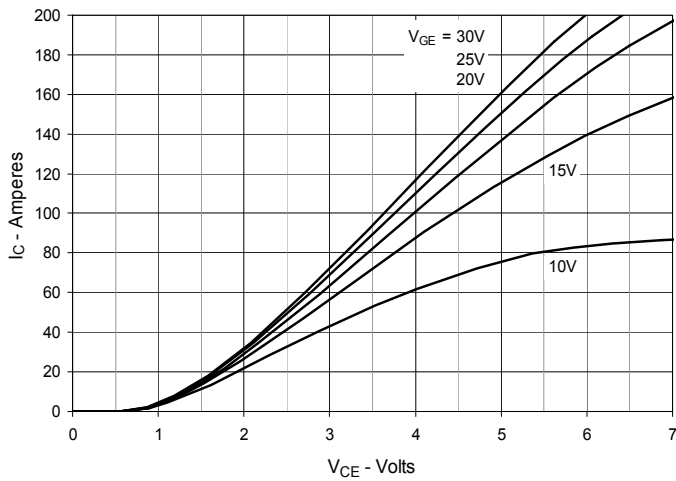


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

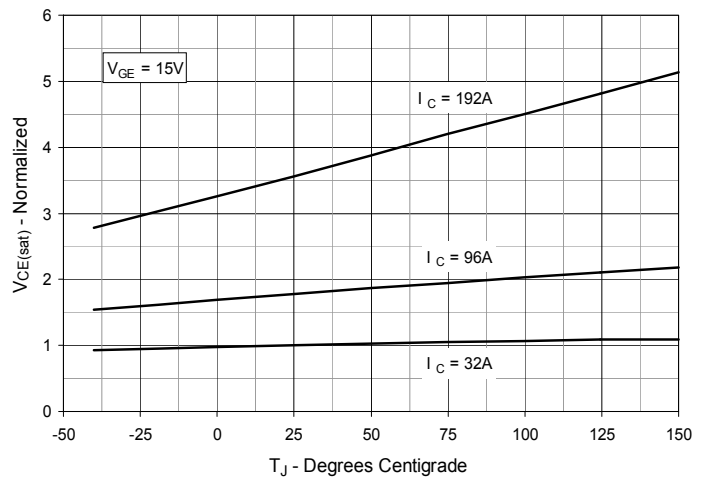


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

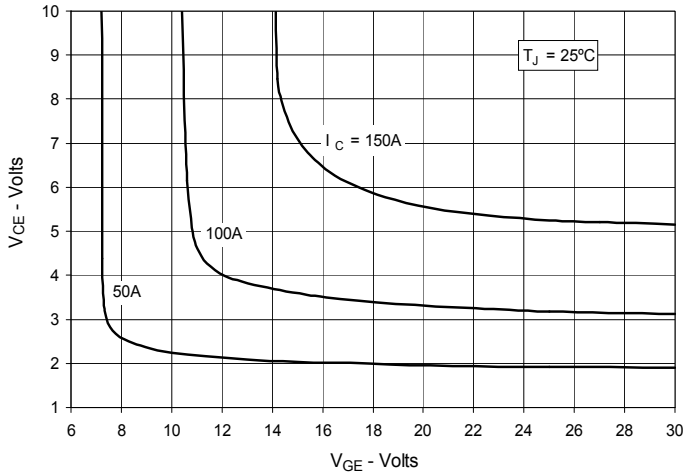


Fig. 6. Input Admittance

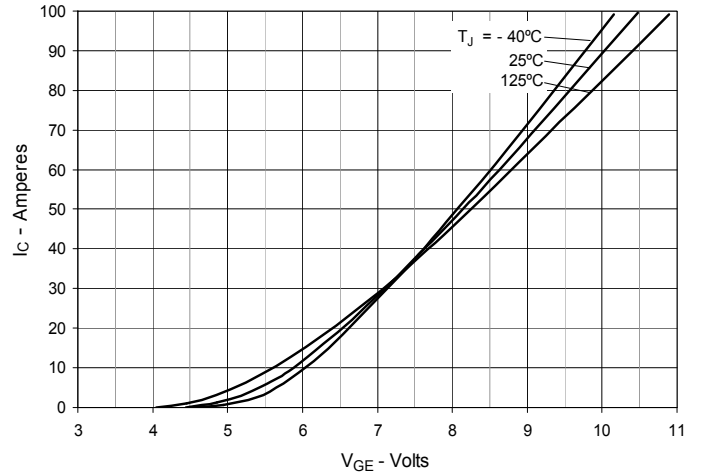


Fig. 7. Transconductance

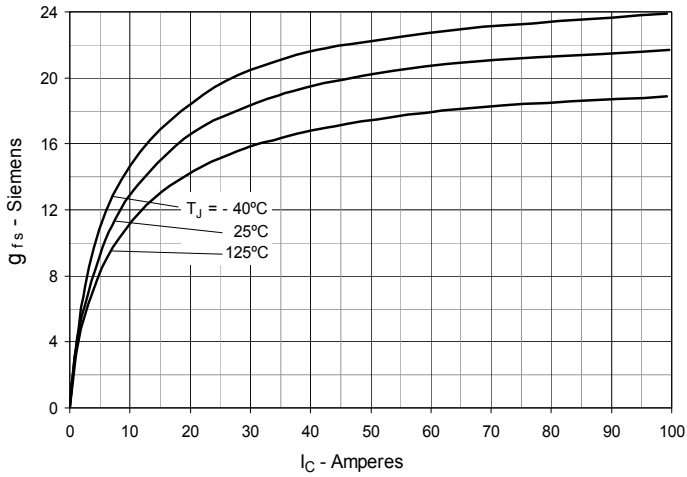


Fig. 8. Dependence of BV_{CES} & $V_{(th)GE}$ on Junction Temperature

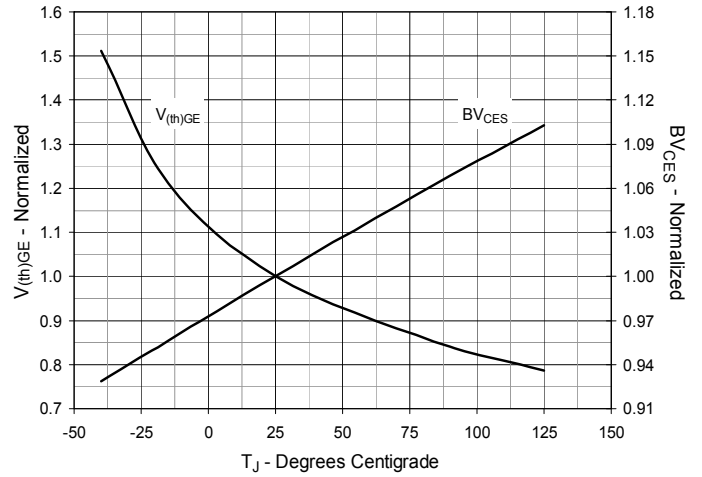


Fig. 9. Single-Pulsed Avalanche Energy vs. Junction Temperature

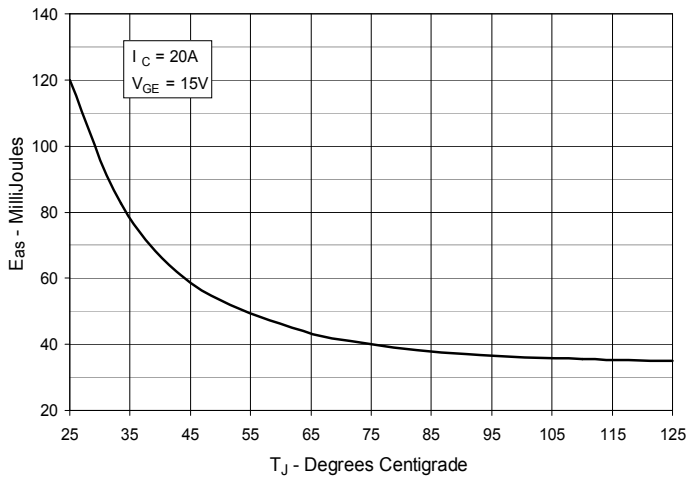


Fig. 10. Resistive Turn-on Rise Time vs. Gate Voltage

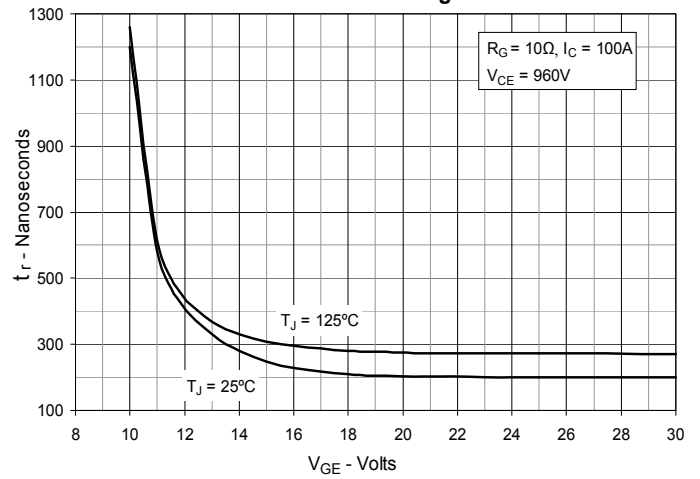


Fig. 11. Gate Charge

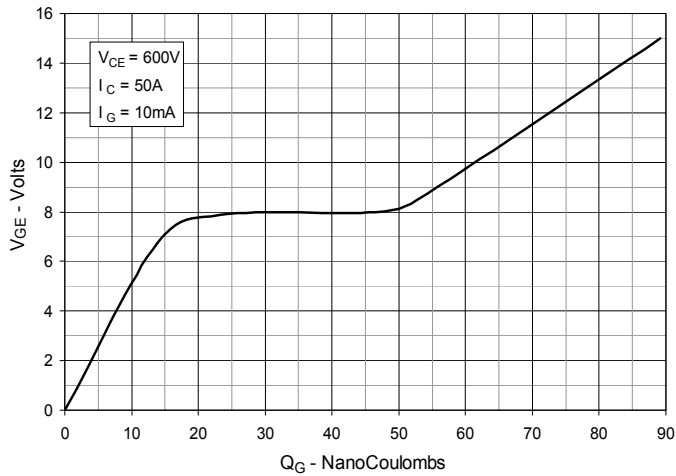


Fig. 12. Capacitance

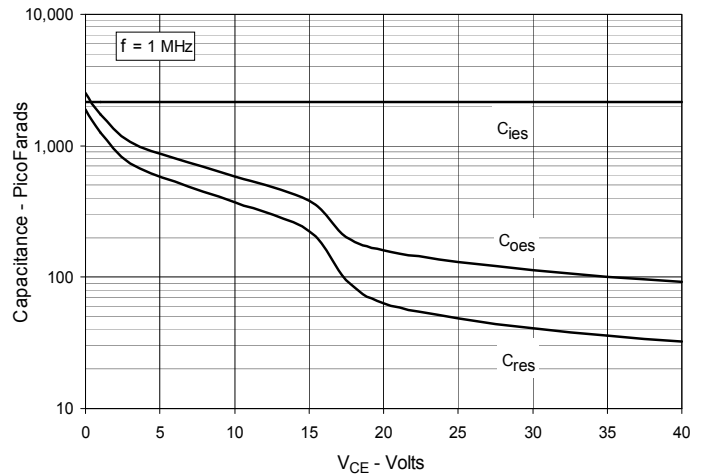


Fig. 13. Resistive Turn-on Switching Times vs. Gate Resistance

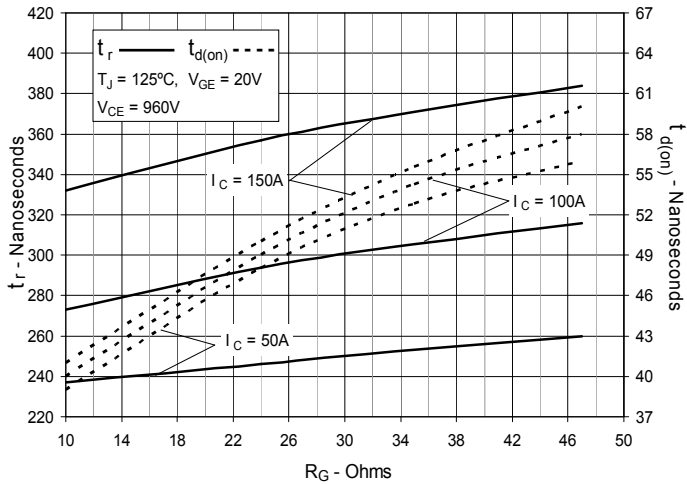


Fig. 14. Resistive Turn-on Rise Time vs. Junction Temperature

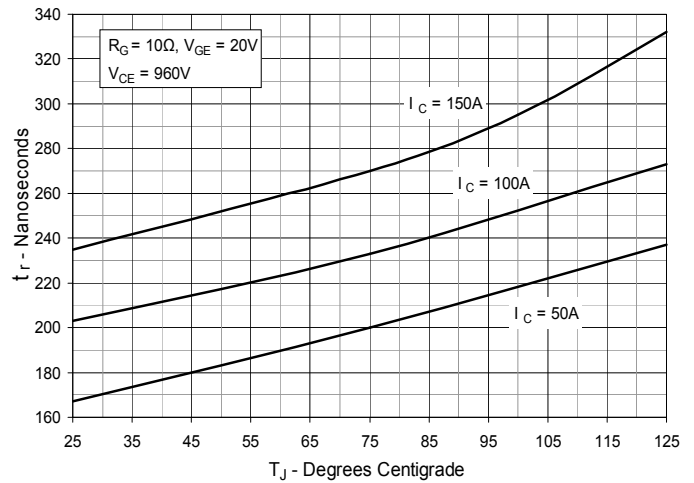


Fig. 15. Resistive Turn-on Rise Time vs. Collector Current

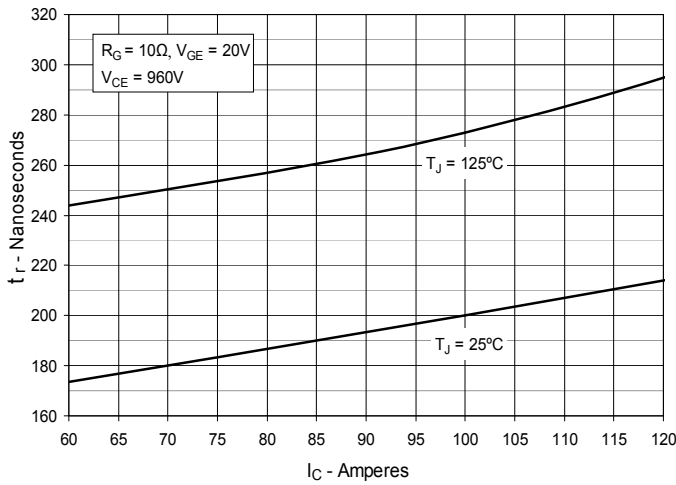


Fig. 16. Resistive Turn-off Switching Times vs. Gate Resistance

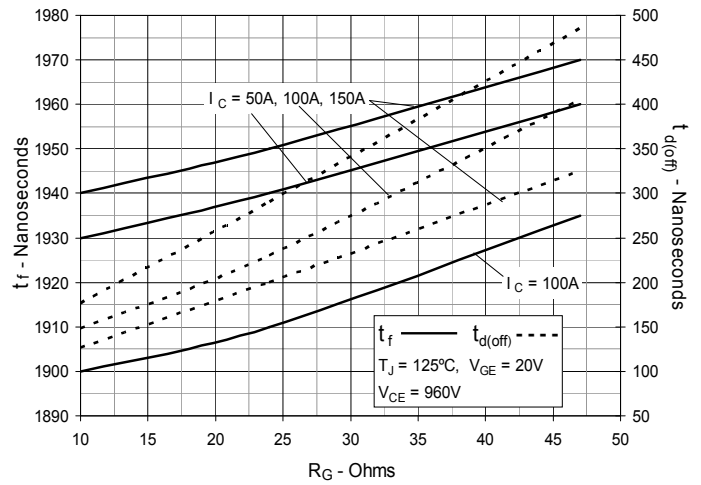


Fig. 17. Resistive Turn-off Switching Times vs. Junction Temperature

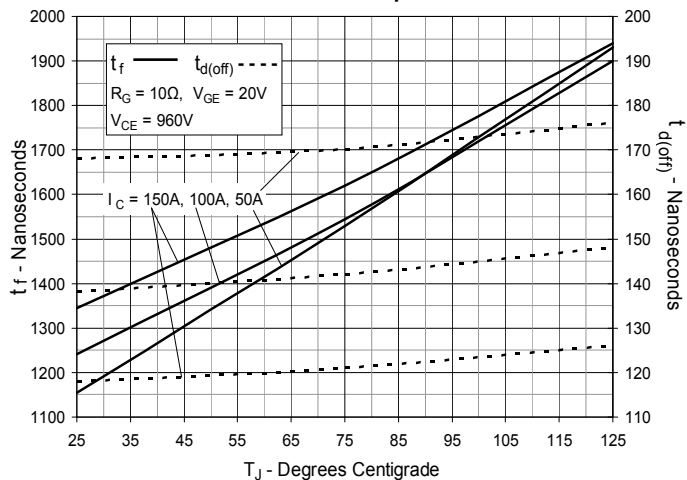


Fig. 18. Resistive Turn-off Switching Times vs. Collector Current

